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APPLICATION NO.	FILIN	IG DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/931,347 08/16/2001		16/2001	Bangalore Aswatha Nagaraj	13DV14035	2644
31316	7590	08/28/2002			
GREGORY	GARMON	1G	EXAMINER		
P.O. BOX 12 ZEPHYR CO	460		MCNEIL, JENNIFER C		
				ART UNIT	PAPER NUMBER
				1775	4
				DATE MAILED: 08/28/2002	

Please find below and/or attached an Office communication concerning this application or proceeding.

ند .					<u>#\&gt;</u>
		Application	No.	Applicant(s)	•
		09/931,347	•	NAGARAJ ET AL.	
	Office Action Summary	Examiner		Art Unit	
		Jennifer M		1775	
Period fo	- The MAILING DATE of this commun r Reply	nication appears on the	cover sheet	with the correspondence addr	ess
THE N - Exten after S - If the - If NO - Failur - Any f	DRTENED STATUTORY PERIOD F MAILING DATE OF THIS COMMUN sions of time may be available under the provision SIX (6) MONTHS from the mailing date of this com period for reply specified above is less than thirty ( period for reply is specified above, the maximum s e to reply within the set or extended period for repl eply received by the Office later than three months d patent term adjustment. See 37 CFR 1.704(b).	IICATION. s of 37 CFR 1.136(a). In no ever munication. 30) days, a reply within the statu: statutory period will apply and will be will be statute cause the appli	ory minimum of t expire SIX (6) M	a reply be timely filed  hirty (30) days will be considered timely.  ONTHS from the mailing date of this comi  ABANDONED (35 U.S.C. § 133).	nunication.
1)[🛛	Responsive to communication(s) f	filed on <u>28 February 20</u>	<u>02</u> .		
2a) <u></u> ☐	This action is FINAL.	2b)⊠ This action is	non-final.		
3)	Since this application is in condition	on for allowance except	for formal n	natters, prosecution as to the	merits is
•	closed in accordance with the pra on of Claims		<i>layle</i> , 1900	0.5. 11, 400 0.0. 210.	
	Claim(s) 1-15 is/are pending in the				
	4a) Of the above claim(s) is/	are withdrawn from cor	nsideration.		
5)□	Claim(s) is/are allowed.				
6)⊠	Claim(s) <u>1-15</u> is/are rejected.				
• -	Claim(s) is/are objected to.				
	Claim(s) are subject to restr	riction and/or election re	equirement.		
• •	ion Papers				
	The specification is objected to by t			to to the butho Everginer	
10)⊠	The drawing(s) filed on <u>16 August 2</u>				
_	Applicant may not request that any o	objection to the drawing(s)	De neid in at	I disapproved by the Evamine	r
11)	The proposed drawing correction fil			_ disapproved by the Examino	. •
_	If approved, corrected drawings are		nce action.		
	The oath or declaration is objected	to by the Examiner.			
	under 35 U.S.C. §§ 119 and 120		1 05 II C	C 5 440(a) (d) or (f)	
ŀ	Acknowledgment is made of a claim		ider 35 U.S.	C. 9 119(a)-(d) or (1).	
a)	☐ All b)☐ Some * c)☐ None of				
	1. Certified copies of the priori				
	2. Certified copies of the priori				
*	<ol> <li>Copies of the certified copies</li> <li>application from the Interest of the attached detailed Office ac</li> </ol>	ernational Bureau (PCT	Rule 17.2(a	1)).	Stage
	Acknowledgment is made of a clain				application).
	a) The translation of the foreign Acknowledgment is made of a clair	language provisional a	oplication ha	s been received.	
Attachme		•			
1)  Not	ice of References Cited (PTO-892) ice of Draftsperson's Patent Drawing Review rmation Disclosure Statement(s) (PTO-1449	v (PTO-948) 3) Paper No(s) <u>2</u> .	4)  Inten 5)  Notic 6)  Other	view Summary (PTO-413) Paper No( e of Informal Patent Application (PTC)	s) O-152)

#### **DETAILED ACTION**

### Claim Rejections - 35 USC § 112

The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

Claims 1-15 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention. Claim 1 refers to an outer layer comprising no more than about 2 wt% Hf. Claims dependent upon claim 1 refer to a gradient of Hf at depths in the protective coating. It is understood that the outer layer is the upper portion of the protective coating and the diffusion layer is the lower portion. However, the specification teaches that the outer layer may be 20 to 40 microns in thickness. The claims teach that at depths of 10-50 microns, the Hf may be 1-9 wt% on average. It is not clear how the outer layer may possess less than 2 wt% on average, when it appears that it overlaps with the depth ranges in which there may be an average of 1-9 wt% Hf. Furthermore, claim 4 states, the Hf concentration has a relatively large second concentration, but is not to exceed 9 wt%, at depths below the protective coating outer surface. The outer surface is on the outer layer, therefore depths below this outer surface include the outer layer. Please clarify.

The claims refer to "the outer layer comprises platinum, aluminum, hafnium, substantially no added silicon, and elements diffused into the protective coating from the substrate". Does this mean that the outer layer has no added silicon, and also has no elements diffused from the substrate? Please clarify.

## Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(a) the invention was known or used by others in this country, or patented or described in a printed publication in this or a foreign country, before the invention thereof by the applicant for a patent.

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Claims 1, 2, 3, and 8 are rejected under 35 U.S.C. 102(a) as being anticipated by Darolia et al (US 6,190,471). Darolia teaches a superalloy article with a coating thereon. The coating includes a protective layer (34) of a diffusion aluminide, such as a platinum aluminide. The protective layer may also include an element such as hafnium. The hafnium is formed in the protective layer by diffusion from the substrate (col. 6, lines 17-67). The protective layer has about 1 wt% Hf after formation of the article (col. 7, lines 13-27). A ceramic layer may be deposited on the aluminide, and the article may be a turbine blade (col. 3, lines 25-30; col. 4, lines 13-17).

(e) the invention was described in-

(1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effect under this subsection of a national application published under section 122(b) only if the international application designating the United States was published under Article 21(2)(a) of such treaty in the English language; or

(2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that a patent shall not be deemed filed in the United States for the purposes of this subsection based on the filing of an international application filed under the treaty defined in section 351(a).

Claims 1-15 are rejected under 35 U.S.C. 102(e) as being anticipated by Darolia et al (US 6,344,282). Darolia et al teach a diffusion aluminide coating having a graded structure. The substrate is a nickel base superalloy with a substrate surface, and the coating has an inner region of a diffusion aluminide including a reactive element such as Hf. A thermal barrier coating (40) may be applied over the aluminide coating. Specifically, Darolia gives an example of Hf added to the aluminide wherein the Hf is disposed in a gradient. At depths of 0-5 microns, the Hf is present at 0.11 wt%; at depths of 5-15 microns, the Hf is present at 0.51 wt%; and at depths of 15-30 microns the Hf is present at 6.9 wt% and Al is present at 20.7 wt %. Also, Darolia gives an example where the Pt is present at 27.5 wt% at 5-15 microns or 29 wt% at 15-30 microns (see examples 4 and 5). Essentially, with increasing distance inward from the outer surface towards the substrate, the reactive element concentration (hafnium) will increase to a peak level and then decrease until the element approaches zero near the surface of the substrate (col. 6, line 65- col. 7, line 4). Darolia also clearly teaches that a diffusion zone will be present when a nickel base superalloy is used (col. 4, lines 55-60).

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#### Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Jennifer McNeil whose telephone number is 703-305-0553. The examiner can normally be reached on Monday through Friday, 9:30AM-6:00PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Deborah Jones can be reached on 703-308-3822. The fax phone numbers for the organization where this application or proceeding is assigned are 703-872-9310 for regular communications and 703-872-9311 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0661.

T (7) 1

August 25, 2002

Jennifer McNeil Examiner

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SUPERVISORY PATENT EXAMINER